

IN THE CLAIMS:

Please amend claim 1, as shown in clean form below.

1. (Twice Amended) A thin film deposition reactor comprising:

    a reactor block on which a wafer is placed;

    a shower head plate for uniformly maintaining a predetermined pressure by covering the reactor block;

    a wafer block installed in the reactor block, on which the wafer is to be seated;

    an exhausting portion connected to the reactor block for exhausting a gas from the reactor block;

    a first connection line in communication with the shower head plate, through which a first reaction gas and/or inert gas flow;

    a second connection line in communication with the shower head plate, through which a second reaction gas and/or inert gas flow; and

    a diffusion plate mounted on a lower surface of the shower head plate, the diffusion plate having a plurality of spray holes which are in communication with the first connection line and face the upper surface of the wafer to spray the first reaction gas and/or inert gas onto the wafer, and a plurality of nozzles which are in communication with the second connection line and extend toward the inner side surface of the reactor block to spray the second reaction gas and/or inert gas toward edges of the wafer, whereby the first and second reaction gases and/or inert gases are independently applied on the wafer without mixing each other.